

STB70NF03L STP70NF03L - STB70NF03L-1

N-channel 30V - 0.0075Ω - 70A - D²PAK - I²PAK - TO-220 Low gate charge STripFET™ II Power MOSFET

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STB70NF03L	30V	< 0.0095Ω	70A
STP70NF03L	30V	< 0.0095Ω	70A
STB70NF03L-1	30V	< 0.0095Ω	70A

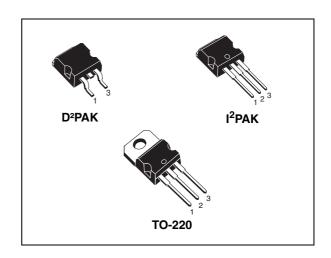
- Conduction losses reduced
- Switching losses reduced

Description

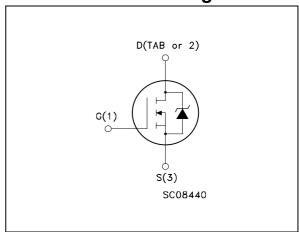
This application specific Power MOSFET is the third genaration of STMicroelectronis unique "Single Feature Size™" strip-based process. The resulting transistor shows the best trade-off between on-resistance and gate charge. When used as high and low side in buck regulators, it gives the best performance in terms of both conduction and switching losses. This is extremely important for motherboards where fast switching and high efficiency are of paramount importance.

Applications

Switching application



Internal schematic diagram



Order codes

Part number	Part number Marking		Packaging
STB70NF03L	B70NF03L	D ² PAK	Tape & reel
STP70NF03L	P70NF03L	TO-220	Tube
STB70NF03L-1	B70NF03L	I ² PAK	Tube

July 2006 Rev 10 1/15

Contents

1	Electrical ratings	. 3
2	Electrical characteristics	
3	2.1 Electrical characteristics (curves)	
4	Package mechanical data	. 9
5	Packaging mechanical data	13
6	Revision history	14

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate voltage ($R_{GS} = 20k\Omega$)	30	V
V _{GS}	Gate- source voltage	± 18	V
I _D	Drain current (continuous) at T _C = 25°C	70	Α
I _D	Drain current (continuous) at T _C = 100°C	50	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	280	Α
P _{TOT}	Total dissipation at T _C = 25°C	100	W
	Derating factor	0.67	W/°C
dv/dt (2)	Peak diode recovery voltage slope	5.5	V/ns
E _{AS} (3)	Single pulse avalanche energy	500	mJ
T _{stg}	Storage temperature	-55 to 175	°C
TJ	Operating junction temperature	-55 10 175	

^{1.} Current limited by the package

Table 2. Thermal data

Symbol Parameter		Value	Unit
R _{thJC}	Thermal resistance junction-case Max	1.5	°C/W
R _{thJA}	Thermal resistance junction-ambient Max	62.5	°C/W
T _I	Maximum lead temperature for soldering purpose	300	°C

^{2.} I_{SD} \$0A, di/dt \$50A/\mu s, V_{DD} \$\leq V_{(BR)DSS}, T_J \$\leq T_{JMAX}\$

^{3.} Starting $T_J = 25$ °C, $I_D = 35A$, $V_{DD} = 25V$

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. ON/OFF states

Symbol	Parameter	Test cond	Min	Тур	Max	Unit	
V _{(BR)DSS}	Drain-source Breakdown voltage	$I_D = 250 \mu A, V_{GS}$	30			٧	
I _{DSS}	Zero gate voltage Drain current (V _{GS} = 0)	$V_{DS} = Max rating$ $V_{DS} = Max rating$ $T_{C} = 125^{\circ}C$			1 10	μA μA	
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 18V				±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$	I _D = 250μA	1			V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V V _{GS} = 5 V	$I_D = 35A$ $I_D = 18A$		0.0075 0.0135	0.0095 0.018	W W

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
9 _{fs} ^(*)	Forward transconductance	$V_{DS} = 15V$ $I_D = 35A$		25		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		1440 560 135		pF pF pF

Table 5. Switching times

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
t _{d(on)} t _r	Turn-on delay time Rise time	$\begin{aligned} &V_{DD} = 15V & I_D = 35A \\ &R_G = 4.7\Omega & V_{GS} = 5V \\ &\textit{Figure 16}. \end{aligned}$		22 165		ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 15V I _D = 70A V _{GS} = 5V		22.5 9 12	30	nC nC nC
t _{d(off)} t _f	Turn-off delay time Fall time	$\begin{aligned} &V_{DD} = 15V & I_D = 35A \\ &R_G = 4.7\Omega, & V_{GS} = 5V \\ &\textit{Figure 16}. \end{aligned}$		21 25		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				70 280	A A
V _{SD} ⁽²⁾	Forward on voltage	$I_{SD} = 70A$ $V_{GS} = 0$			1.3	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 70A \text{ di/dt} = 100A/\mu s$ $V_{DD} = 20V \qquad T_J = 150^{\circ}C$ Figure 15.		42 52 2.5		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

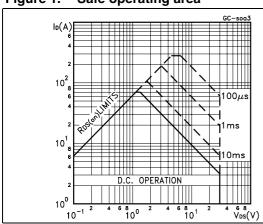


Figure 2. Thermal impedance

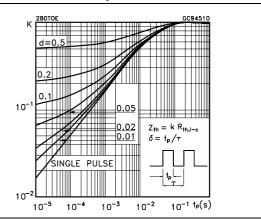


Figure 3. Output characterisics

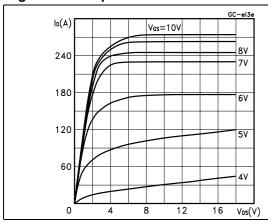


Figure 4. Transfer characteristics

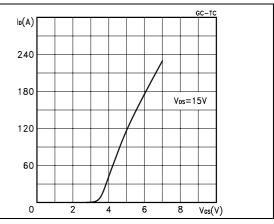


Figure 5. Transconductance

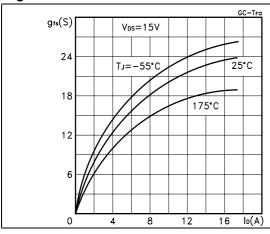
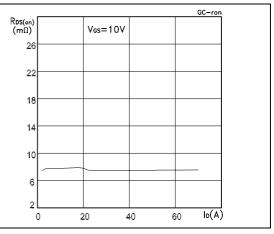


Figure 6. Static drain-source on resistance



Vgs(V) C(pF) f=1MHz Vgs=0V Vos=15V lo=70A 4000 3000 2000 1000 8 24 32 Q_g(nC) 0 18 6 12 24 V_{DS}(V)

Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

Figure 9. Normalized gate threshold voltage vs temperature

Figure 10. Normalized on resistance vs temperature

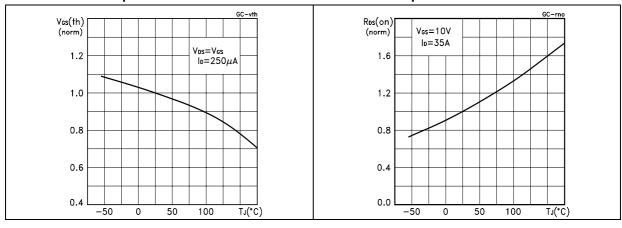
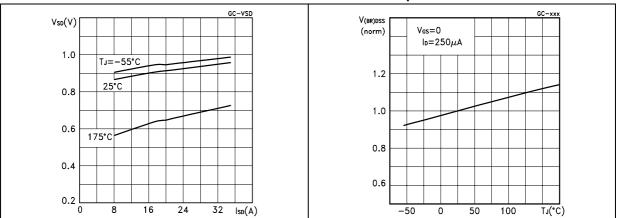


Figure 11. Source-drain diode forward characteristics

Figure 12. Normalized Breakdown vs temperature



5//

3 Test circuit

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

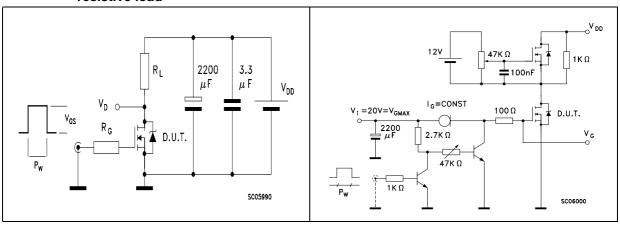


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

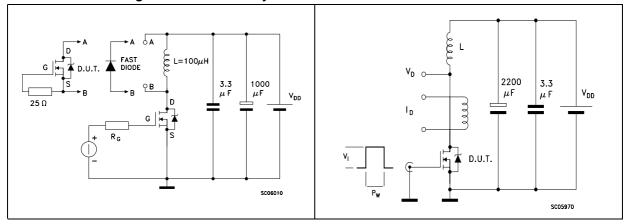
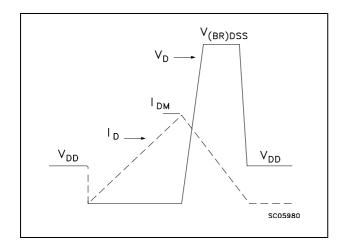


Figure 17. Unclamped inductive waveform



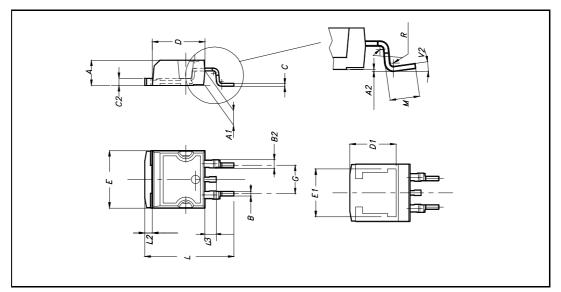
577

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

D²PAK MECHANICAL DATA

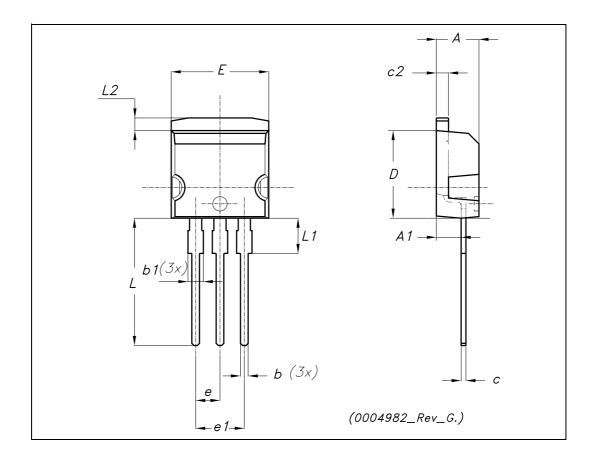
D.I.I.		mm. inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
Е	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0₀		4º			



Ay/

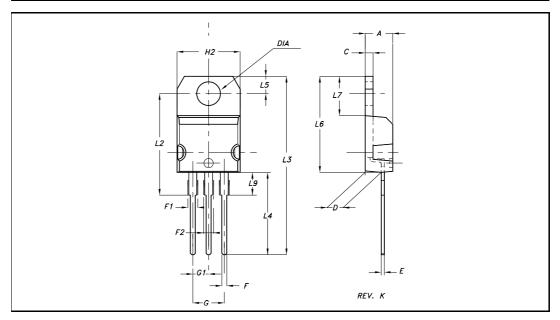
TO-262 (I²PAK) MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
Е	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



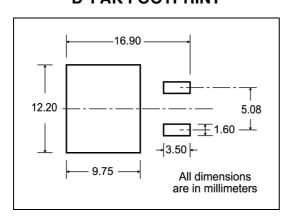
TO-220 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.066
F2	1.14		1.70	0.044		0.066
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.259
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151

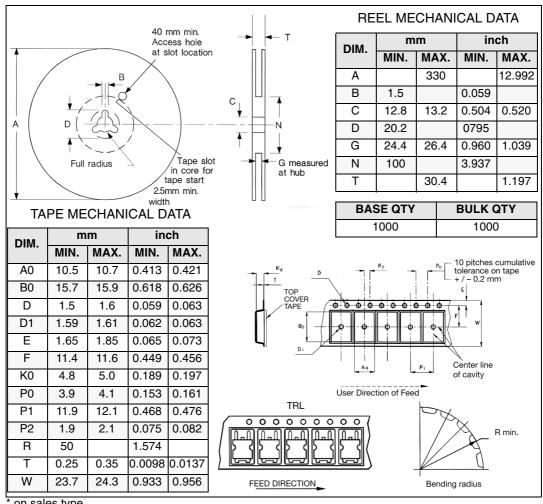


577

Packaging mechanical data 5 D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
21-Jun-2004	9	Preliminary version
25-Jul-2006	10	New template, no content change

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

577